

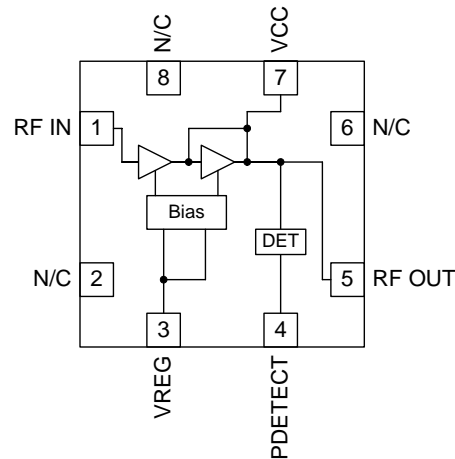


Features

- Single Power Supply 1.8V to 3.6V
- Very Low Current (see table for all modes)
- >5dBm 11g P_{OUT}@<1% and 10dBm 11g P_{OUT}@≤4%
- P_{OUT}=19dBm Meeting Class 1 BT
- Gain: 28dB Typ 11b/g/BT

Applications

- IEEE802.11b/g/n Driver/Amplifier
- General Purpose Amplification
- Class 1 Bluetooth Power Amplifier
- Driver Amplifier for TX Power Amplifier



Functional Block Diagram

Product Description

The RF5373 is a linear driver/amplifier that meets the FCC and ETSI requirements for operation in the 2.4GHz to 2.5GHz (IEEE802.11b/g/n and BT Class 1) bands. Operating from a single 1.8V to 3.6V supply, the amplifier will easily be incorporated into WLAN designs with minimal external components. The device is manufactured on an advanced InGaP Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process. The device is provided in a 2.2mmx2.2mmx0.6mm, 8-pin, QFN with a backside ground.

Ordering Information

RF5373	1.8V to 3.6V IEEE802.11b/g/n and Bluetooth Driver/Amplifier
RF5373PCBA-41X	Fully Assembled Evaluation Board
RF5373PCBA-410	IEEE802.11b/g 2.4GHz to 2.5GHz Operation

Optimum Technology Matching® Applied

- | | | | |
|---|--------------------------------------|-------------------------------------|-----------------------------------|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | |
| <input checked="" type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | |

RF5373



rfmd.com

**Please contact
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for more information.**